

Single-Shot Readout Performance of Two Heterojunction-Bipolar-Transistor Amplification Circuits at Millikelvin Temperatures

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High-fidelity single-shot readout of spin qubits requires distinguishing states much faster than the T_1 time of the spin state. One approach to improving readout fidelity and bandwidth (BW) is cryogenic amplification, where the signal from the qubit is amplified before noise sources are introduced and room-temperature amplifiers can operate at lower gain and higher BW. We compare the performance of two cryogenic amplification circuits: a current-biased heterojunction bipolar transistor circuit (CB-HBT), and an AC-coupled HBT circuit (AC-HBT). Both circuits are mounted on the mixing-chamber stage of a dilution refrigerator and are connected to silicon metal oxide semiconductor (Si-MOS) quantum dot devices on a printed circuit board (PCB). The power dissipated by the CB-HBT ranges from 0.1 to 1 μ W whereas the power of the AC-HBT ranges from 1 to 20 μ W. Referred to the input, the noise spectral density is low for both circuits, in the 15 to 30 fA/ $\sqrt{\text{Hz}}$ range. The charge sensitivity for the CB-HBT and AC-HBT is 330 $\mu\text{e}/\sqrt{\text{Hz}}$ and 400 $\mu\text{e}/\sqrt{\text{Hz}}$, respectively. For the single-shot readout performed, less than 10 μs is required for both circuits to achieve bit error rates below 10^{-3} , which is a putative threshold for quantum error correction.

INTRODUCTION

Spin qubits in semiconductors are a promising platform for building quantum computers^{1–8}. Significant progress has been achieved in recent years, including demonstrations of extremely long coherence times⁹, high-fidelity state readout^{10–13}, high-fidelity single qubits gates^{9,14–16}, and two qubit gates^{7,16–18}. As the field advances to multiple qubit systems, improvements in single-shot state readout and measurement times will be necessary to achieve fault tolerance. Improving the signal-to-noise ratio (SNR) and bandwidth (BW) of the qubit state detection is critical for both tunnel rate selective readout² and energy selective readout³. With the same bit error rate, faster readout will reduce tunnel rate and metastable relaxation or relaxation related errors.

Cryogenic amplification is one way the readout SNR and BW can be improved. Challenges are that: 1) input signals remain relatively small^{19–23} and 2) significant noise and parasitic capacitance is introduced into the measurement circuit when routing the signal out of a dilution refrigerator²⁴. Several approaches for cryogenic amplification include: radio-frequency (RF) resonant quantum point contact (QPC) and single electron transistor (SET) circuits^{25–32}, gate dispersive RF circuits³³, Josephson parametric amplification circuits³⁴, and cryogenic transistors^{35–39}. For single-shot readout, qubit state distinguishability with sensitivity 140 $\mu\text{e}/\sqrt{\text{Hz}}$ has been demonstrated²⁹. However, many of these circuits require elements to be mounted at multiple fridge stages and the use of custom on-chip components, adding to the complexity of their implementation.

Simpler amplification circuits that use low power transistors mounted directly on the mixing chamber stage with the qubit device thus have significant appeal^{38,39}. For example, a proof of principle readout demonstration with a dual stage HEMT achieved $T_e = 240$ mK, gain = 2700 A/A, power = 13 μ W, noise referred to input ≤ 70 fA/ $\sqrt{\text{Hz}}$, and 350 $\mu\text{e}/\sqrt{\text{Hz}}$ charge sensitivity³⁹.

Silicon-germanium (SiGe) heterojunction bipolar transistors (HBTs) have been demonstrated to operate at liquid helium temperatures^{38,40} as well as millikelvin temperatures in dilution refrigerators^{41–44}. The HBT is motivated by low $1/f$ noise, high R_{out} , and possible opportunities to achieve higher gain at the same power. Furthermore, there can be bipolar junction transistor (BJT) advantages compared to field effect transistors (FETs) for low input impedance amplifier circuits⁴⁵. Our approach is to use a single SiGe HBT as a cryogenic amplifier at the mixing chamber stage of a dilution refrigerator to improve the SNR and BW of the signal from a SET used as a charge-sensor. We have designed and characterized two different HBT circuits: 1) the current-biased HBT circuit (CB-HBT) (Figure 2(a)) and 2) the AC-coupled HBT circuit (AC-HBT) (Figure 1(a)). The CB-HBT simply has the drain of the SET connected to the base of the HBT, while the AC-HBT has the base of the HBT connected to the drain of the SET via a resistor-capacitor (RC) bias tee. Regardless of the coupling between the HBT and SET, the HBT must be DC biased in order to amplify. For either circuit, the silicon metal oxide semiconductor (Si-MOS) device and HBT are mounted on a printed circuit board (PCB) only centimeters apart. The proximity of the HBT amplifier to the SET has the ad-

vantages of minimizing parasitic input capacitance and increasing signal before noise from the fridge is added. However, since the mixing chamber stage has a cooling power of around $100 \mu\text{W}$ at 100 mK , the HBT circuits must operate with powers similar or less in order to avoid heating.

In this letter, we first introduce the two amplification circuits with discussions of gain, sensitivity, bias behavior, and noise. We compare the basic performance and operation of the two amplifiers and extract input-referred noise as well as signal response and heating of the quantum dot electrons. Finally, we compare and discuss the performance for single-shot readout, which somewhat depends on the specific layout of the SET and quantum dot to produce larger signals via increased mutual capacitance.

AC-HBT DESCRIPTION

The AC-HBT consists of a Si-MOS device that is AC-coupled to an HBT, which amplifies the SET response to AC source-drain voltage excitation at frequencies higher than around 100 Hz . The SET is integrated into a double quantum dot (QD) device (Figure 1(a): SEM image), which is made on a Si-MOS platform (see Appendix A).

To operate the AC-HBT, the DC base bias is grounded, and the emitter is biased negatively to support a base-emitter bias V_{BE} above the cryogenic HBT threshold (about -1.04 V). The HBT current at the collector is measured through a room temperature transimpedance amplifier (TIA), and the signal is demodulated, filtered, and digitized. The TIA is referenced to ground, so the collector-emitter bias equals the base-emitter bias. We find that this configuration optimizes the circuit SNR and also requires only two lines coming from room temperature for the three HBT terminals. Figure 1(c) shows the total AC circuit gain and sensitivity vs. the amount of power dissipated by the HBT. The AC gain is measured by comparing the current of a Coulomb blockade (CB) peak with and without the HBT. The SET current can be measured directly by connecting the output of R_S to a room temperature TIA (lowest ground in Figure 1(a)). The sensitivity of the circuit is defined as the gate-voltage derivative of collector-current (slope) on the side of a CB peak, which is the typical bias point where readout occurs. Sensitivities of $1\text{--}5 \mu\text{A/V}$ are achieved in the operating region of the AC-HBT. Since the AC-HBT is a linear amplifier, the shape of a CB peak remains unaffected by different gain/sensitivity bias points of the AC-HBT (Figure 1(d)). The AC bias across the SET was chosen to be $200 \mu\text{V}_{\text{RMS}}$ in this case to minimize the electron temperature below 200 mK .

Noise spectra are collected for different AC-HBT biases (see Appendix F), and noise at around 74 kHz is referred to the HBT collector and studied. The noise displays two different behaviors as power dissipated is increased (Figure 1(e)). The transconductance of the transistor ($\frac{dI_C}{dV_{BE}}$)

increases with power, so it is important to identify where the transistor begins to add appreciable noise. In the low-power limit, the noise dependence is approximately flat at around $1 \text{ pA}/\sqrt{\text{Hz}}$, which we attribute to the noise after the HBT dominating any AC-HBT noise. As the AC-HBT power is increased to $> 1 \mu\text{W}$, the noise becomes linearly dependent on power. This behavior is predicted by our estimated shot noise for the base current (Figure 1(e) orange curve). The estimated total noise is calculated by adding all noise source predictions in quadrature (dark red curve) and aligns well with the total measured noise (blue points).

CB-HBT DESCRIPTION

The CB-HBT circuit consists of an HBT wire bonded from its base terminal directly to the drain of the SET. The SET is integrated into a double QD system consisting of a lithographic QD and a secondary object that has not been definitively identified (i.e., either a QD⁴⁶ or donor²³). A high-frequency coaxial line is connected to the collector of the HBT which is used to measure the readout current (Figure 2(a)). This collector line is connected to a TIA which is set with gain 10^5 V/A and -3 dB bandwidth 400 kHz unless otherwise noted. The output of the TIA is connected to a voltage amplifier used to limit the bandwidth or further amplify the signal. Finally, the output of the voltage amplifier is connected to an oscilloscope with an adjustable sample rate.

Operation of the circuit requires the emitter of the HBT to be connected to a room temperature power supply filtered to 1 MHz (to suppress higher frequency noise) and biased between -1.03 and -1.07 V . The bias of the emitter power supply sets the base current, collector current, gain, and dissipated power of the HBT. In Figure 2(b), the DC current gain and sensitivity are plotted as a function of power. The DC current gain is defined as $\frac{I_C}{I_B}$, and the sensitivity is defined as before. The sensitivity of the CB-HBT can reach $5 \mu\text{A/V}$ between $100\text{--}500 \text{ nW}$, whereas the AC-HBT requires $> 10 \mu\text{W}$ to reach a similar sensitivity.

The CB-HBT acts as a current bias, so there is always current through the SET (see Appendix B). In regions of Coulomb blockade, the HBT base-emitter voltage will shift on the order of the charging energy of the SET in order to maintain a relatively constant current through the circuit. To show the current-biasing effect, a CB peak is plotted for different CB-HBT gain values in Figure 2(d), and the current is normalized to the value at the top of the CB peak. Although the current in the blocked regions of the CB peak is much different from a voltage-biased configuration, the slope of the sides of the CB peak appear to be less affected by the current-biasing (sensitivities of $1\text{--}5 \mu\text{A/V}$ are achieved for either circuit). We note that the effect of current bias on Coulomb blockade is independent of the HBT presence (Figure 7).

As with the AC-HBT, the noise referred to the collec-

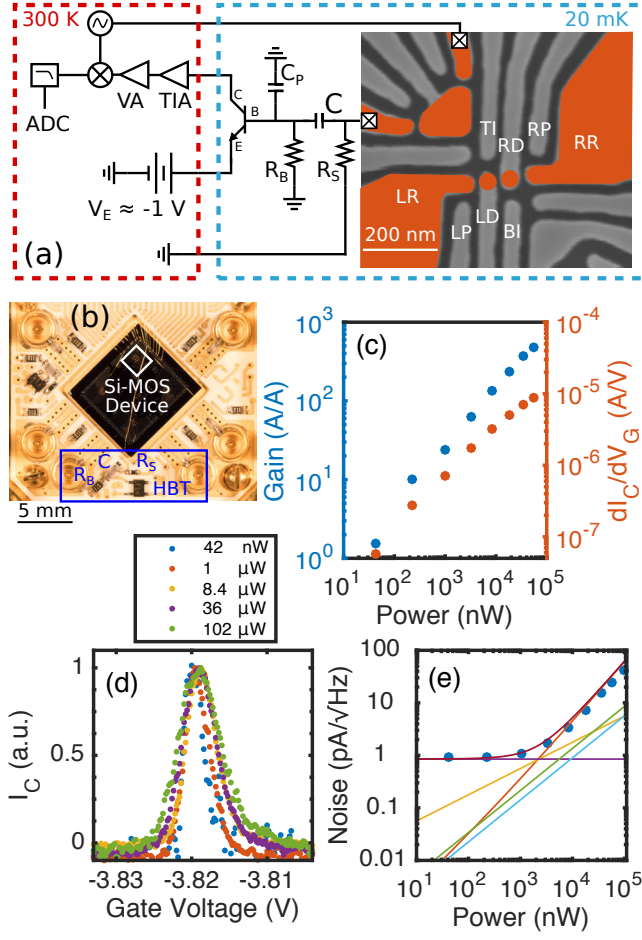


Figure 1. (a) Schematic diagram of AC-HBT and SEM image of the double quantum dot (DQD) device. Areas of electron accumulation are indicated by false color highlighting of enhancement gates. The charge sensor used to measure the DQD state is in the upper left quadrant, whose source is connected to an AC+DC signal generator, and whose drain is connected to a cryogenic AC-coupled HBT amplification stage. The amplification stage is mounted at the dilution refrigerator mixing chamber on the same printed circuit board as the DQD device. Values of the passive elements are $R_B = 1 \text{ M}\Omega$, $R_S = 100 \text{ k}\Omega$, and $C = 10 \text{ nF}$. (c) Circuit gain and sensitivity vs. power dissipated by the AC-HBT. (d) Normalized CB peak for different AC-HBT gain/power biases. The the blockade region of the CB peak reaches zero current. (e) Noise referred to the collector of the AC-HBT for different powers. The measured noise is plotted as blue points. The noise floor of the fridge (purple), shot noise of the base (orange), collector (yellow), SET (light blue), Johnson noise of the shunt resistor (green), and total estimated noise (dark red) are plotted as solid lines.

tor of the CB-HBT is examined at around 7 kHz (Figure 2(d)). Similar qualitatively, the lower power region is dominated by noise after the HBT around $1 \text{ pA}/\sqrt{\text{Hz}}$ (purple curve). As power is increased, the measured noise (blue points) begins to increase, which follows the estimated behavior of the base current shot-noise (orange

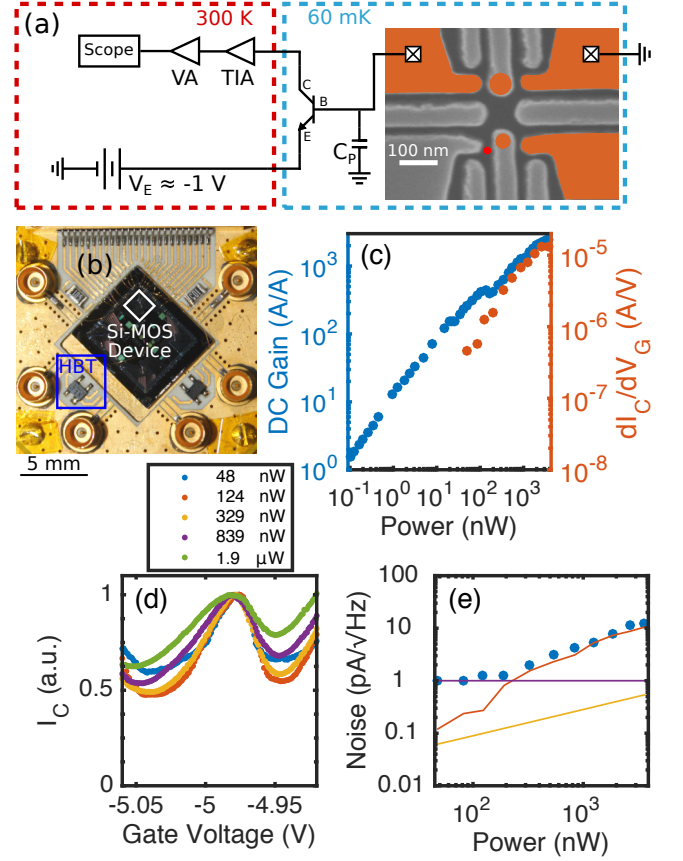


Figure 2. (a) Schematic diagram of CB-HBT readout circuit including room temperature amplification and biasing. The SET is represented by the larger, upper orange circle, and the QD is represented by the smaller, lower orange circle. (b) Image of the PCB which shows the Si-MOS device and HBT mounted close together. (c) DC current gain and sensitivity vs. power dissipated by the CB-HBT. (d) Normalized CB peak for different CB-HBT gain/power biases. The blocked regions of the CB peak do not reach zero current. (e) Noise referred to the collector of the CB-HBT for different powers. The measured noise is plotted as blue points. For comparison, the noise floor of the fridge (purple curve), base current shot noise (orange curve), and collector current shot noise (yellow curve) are plotted as well.

curve) (see Appendix F).

AMPLIFIER PERFORMANCE COMPARISON

We next compare the performance of both amplifiers with respect to power dissipated. The first metric examined is gain as power is increased. The gain of the AC-HBT is simply the measured gain of the amplifier, however the gain of the CB-HBT circuit is not as simple to extract. The small-signal resistance of the SET (r_{set}) must be known in order to calculate the CB-HBT gain (see Appendix E). Since the SET is directly connected to the HBT, we cannot measure r_{set} . Instead,

we use the value of r_{set} ($3 \text{ M}\Omega$) which best follows the measured noise behavior in Figure 2(e) to estimate the gain. We plot this estimated gain of the CB-HBT circuit and compare to the measured gain of the AC-HBT circuit in Figure 3(a). We observe that the CB-HBT circuit achieves higher gain at lower powers, including operating with gain over 400 at a power around $1 \text{ }\mu\text{W}$.

We next compare the noise referred to the input of the HBT for each circuit. Noise is referred to the input using the gain values in Figure 3(a). We measure the noise spectrum for each circuit at different bias points and choose the frequency which minimizes the noise. The frequency chosen for the AC-HBT circuit was around 74 kHz , and the frequency for the CB-HBT circuit was around 7 kHz . When the input-referred noise is plotted as a function of power (Figure 3(b)), we observe a minimum noise operating point for either circuit. At low powers, the noise is likely dominated by triboelectric noise due to the fridge and input noise of the room temperature TIA. At higher powers, the HBT amplifiers begin injecting appreciable noise into the circuit, therefore the overall noise increases. The CB-HBT circuit achieves a minimum noise of $19 \text{ fA}/\sqrt{\text{Hz}}$ at a power around 800 nW , while the AC-HBT circuit achieves a minimum noise of $26 \text{ fA}/\sqrt{\text{Hz}}$ at a power around $8.4 \text{ }\mu\text{W}$.

For the powers that minimize noise for each circuit, we plot the input-referred noise spectrum for both circuits as a function of frequency (Figure 3(c)). The noise spectrum of the CB-HBT is plotted out to 100 kHz , since its bandwidth is less than 100 kHz . The $1/f$ -like behavior of the noise at lower frequencies is assumed to be due to charge noise in the Si-MOS device. In the overlapping region around 10 kHz , the noise for the CB-HBT is significantly lower than the noise for the AC-HBT.

Figure 3(d) shows the frequency dependence of an input signal for both amplification circuits up to 1 MHz . The AC-HBT has a -3 dB point at around 650 kHz , and the CB-HBT has a -3 dB point at around 20 kHz , which implies significantly lower BW than the AC-HBT. The origin of this lower BW is not well understood. Using pessimistic numbers, the frequency pole of the SET resistance (assuming $1 \text{ M}\Omega$) and the parasitic capacitance between the SET and the base junction (assuming 1 pF) should only limit the -3 dB point to around 160 kHz . In addition, 4 K simulations of this circuit also yielded around 160 kHz -3 dB BW⁴⁷. Improvements and understanding of the BW of the CB-HBT will be important in future work.

Heating of electrons in the QD due to the operation of the connected HBT is a concern, therefore we examined the dependence of electron temperature on HBT amplifier bias (Figure 3(e)). For the CB-HBT, we find that the minimum electron temperature observed is around 150 mK . Heating of the QD begins where the CB-HBT is operating with over 100 gain at 100 nW , therefore the CB-HBT circuit can amplify well with an electron temperature around 160 – 200 mK . For the AC-HBT, the minimum electron temperature was around 120 mK . When

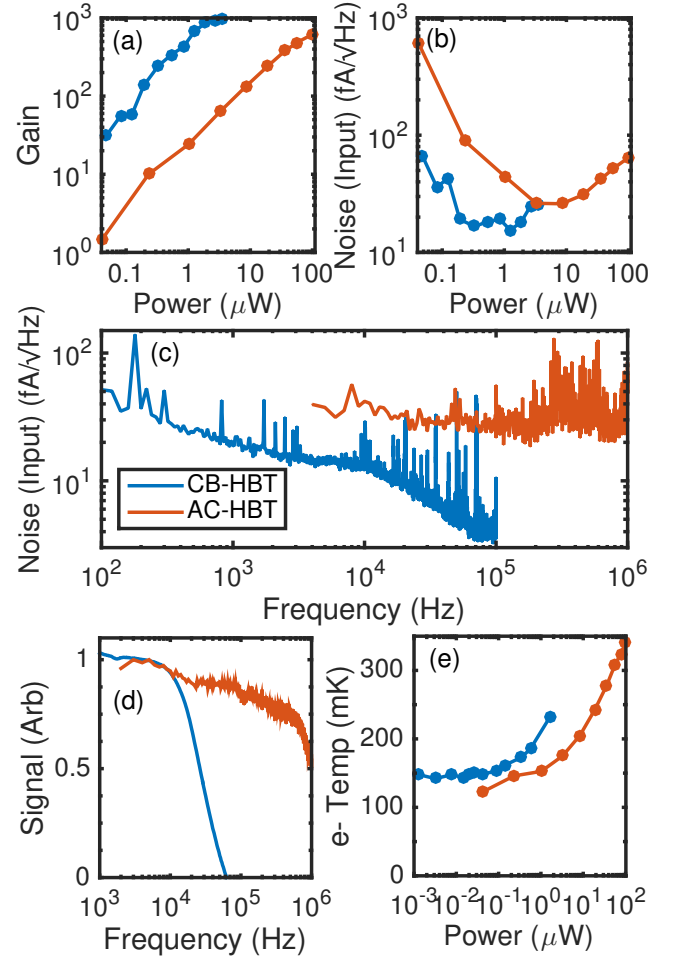


Figure 3. (a) Gain of both circuits as a function of power. Calculated gain of the CB-HBT is shown (Appendix E). (b) Minimum input-referred noise as a function of power. CB-HBT has minimum of $19 \text{ fA}/\sqrt{\text{Hz}}$ at 800 nW , and AC-HBT has minimum of $26 \text{ fA}/\sqrt{\text{Hz}}$ at $8.4 \text{ }\mu\text{W}$. (c) Input-referred noise spectrum of both circuits for power that minimizes noise. (d) Signal response (in normalized arbitrary units) for both circuits as a function of frequency. The CB-HBT has a -3 dB point at around 20 kHz , and the AC-HBT has a -3 dB point at around 650 kHz . (e) Electron temperature vs. power for both circuits. Base electron temperatures are between 120 – 150 mK .

the AC-HBT bias is increased up to $3.24 \text{ }\mu\text{W}$, the electron temperature remains near the minimum temperature. For powers above this threshold, the electron temperature increases approximately linearly with power. Nonetheless, an electron temperature of 200 mK is used for the bias condition that provides the minimum amplifier noise.

SINGLE-SHOT RESULTS COMPARISON

We compare both HBT amplifiers by performing single-shot readout of latched charge states¹⁰. Both Si-

MOS quantum dot devices are tuned to the few electron regime and the spin filling of the last few transition lines are verified with magnetospectroscopy. Figure 4(a) shows the result of a three-level pulse sequence in the AC-HBT device where: 1) the system is initialized into (1,0), 2) ground and excited states are loaded in (2,0), and finally 3) the measurement point (signal plotted) is rastered about the (2,0)-(1,1) anti-crossing. When measuring for 30 μ s, three latched lines are present, which indicates spin blockade for an excited state triplet (T), a second excited state triplet (O), and a lifting of the spin blockade for the ground state singlet (S). We assign T as a valley triplet with valley splitting of 140 μ eV and the O as an orbital triplet with orbital splitting of 280 μ eV. For all single-shot measurements, we remove the state O from the available state space by energy selective loading of the (2,0) state.

For both circuits, a mixture of (2,1) and (2,0) charge states are read out in the reverse latching window. Figure 4(b) shows 100 individual single-shot traces of the readout portion of the pulse for the AC-HBT device. Significant feedthrough is observed in the first few μ s of the readout pulse, likely due to attenuators connecting the conductor of the high BW lines to the ground of other lines including the emitter bias line. State distinguishability does not begin to occur until about 4 μ s, and then the pulse relaxes to two distinct states after about 7 μ s. Extracting the SNR from these traces is done by waiting a certain amount of time, t_{delay} , and then averaging the signal for a certain amount of time, $t_{\text{integration}}$. Histograms of the delayed and averaged shots are compiled and fit to a double Gaussian distribution (Figure 4(c)). The signal is defined as the separation of the Gaussian peaks and the noise is defined as the average of the widths of the Gaussian peaks.

The extracted SNR for a given delay and total time ($t_{\text{delay}} + t_{\text{integration}}$) is plotted in Figures 4(d)&(e). Contours are drawn for each SNR integer on both plots, where the leftmost part of a contour line reveals the minimum total measurement time required to reach a given SNR. We plot the SNR vs. minimum total measurement time in Figure 4(f) for both circuits. The CB-HBT reaches greater SNR at any given time in the 15 μ s plot range. Both circuits achieve SNR > 7 in $t_{\text{total}} < 10 \mu$ s, which corresponds to a bit error rate < 10^{-3} and marks a significant improvement over the equivalent $t_{\text{total}} = 65 \mu$ s in previous work¹⁰. In particular, the CB-HBT is able to reach SNR > 7 in $t_{\text{total}} \approx 6 \mu$ s, which represents over a factor of ten improvement from the previous work¹⁰. The charge sensitivity for the CB-HBT is 330 μ e/ $\sqrt{\text{Hz}}$ ($\tau_{\text{int}} = 6 \mu$ s, SNR = 7.4), and the charge sensitivity for the AC-HBT is 400 μ e/ $\sqrt{\text{Hz}}$ ($\tau_{\text{int}} = 9 \mu$ s, SNR = 7.5). We note that the SET in the CB-HBT device had around 34% more signal due to larger mutual capacitance (Appendix

A) which may contribute to the larger SNRs.

The AC-HBT requires more relative overhead for implementation than the CB-HBT. The AC-HBT includes three additional surface mounted passive elements (Figure 1(a)), which can be optimized to produce better SNR. Additionally, the AC-HBT has a two-dimensional bias space via the base bias and emitter bias, whereas the CB-HBT is only biased via the emitter bias. However, the AC-HBT is a linear gain circuit and can be used with discrete HEMTs⁴⁸ and HBTs, providing more opportunity to optimize the transistor. Ideally, the transistors would have greater transconductance (g_m) and a more ideal dependence on I_C than the HBTs used in this work (see Appendix D). In the present demonstration of the AC-HBT, heating of electrons occurred at powers which minimized noise. Introducing a second AC-HBT stage is relatively straightforward and may allow the first stage to run at powers which don't heat the electrons and minimize the noise further. In addition, the second stage could be mounted further away from the Si-MOS PCB and reduce local heating.

CONCLUSION

We compare the performance of two cryogenic amplification circuits: the CB-HBT and the AC-HBT. The power dissipated by the CB-HBT ranges from 0.1 to 1 μ W, whereas the power of the AC-HBT ranges from 1 to 20 μ W. Referred to the input, the noise spectral density is low for both circuits in the 15 to 30 fA/ $\sqrt{\text{Hz}}$ range. The charge sensitivity for the CB-HBT and AC-HBT is 330 μ e/ $\sqrt{\text{Hz}}$ and 400 μ e/ $\sqrt{\text{Hz}}$, respectively. For single-shot readout performed, both circuits achieve SNR > 7 and bit error rate < 10^{-3} in times less than 10 μ s.

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This paper describes objective technical results and analysis. Any subjective views or opinions that might be expressed in the paper do not necessarily represent the views of the U.S. Department of Energy or the United States Government.

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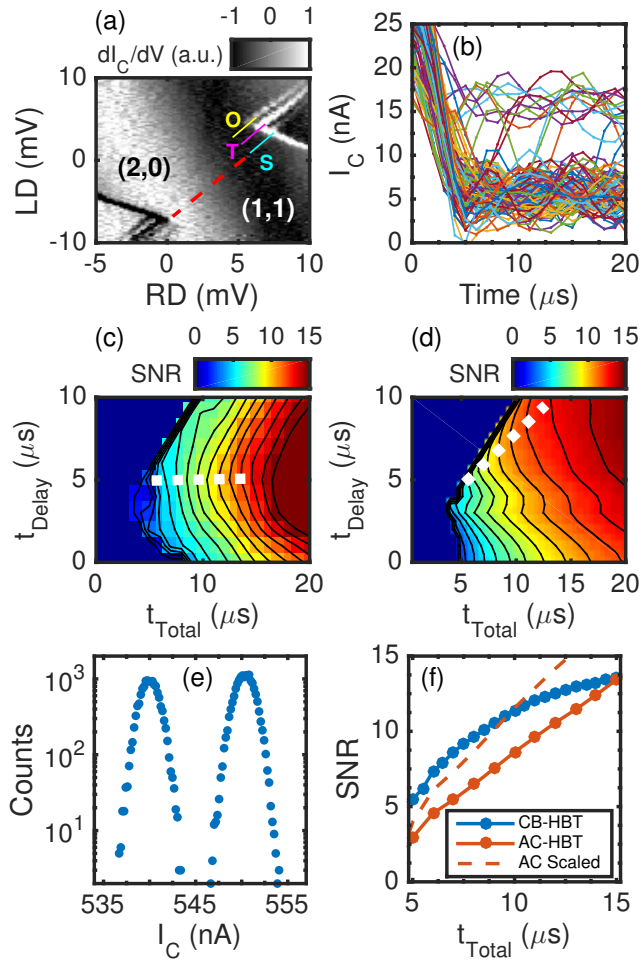


Figure 4. (a) Measurement pulse signal (derivative) rastered about the (2,0)-(1,1) anti-crossing for the AC-HBT device. Three distinct latched lines are present. (b) 100 single-shot traces of the readout portion of the pulse for the AC-HBT device. Signal separation begins to occur around $4 \mu\text{s}$. (c) Example histogram from the CB-HBT readout. (d) 2D SNR plot for the CB-HBT readout. (e) 2D SNR plot for the AC-HBT readout. (f) SNR vs. minimum total measurement time for both circuits, which corresponds to the white dashed line in (c) and (d). The greater gain of the CB-HBT compensates for the lower bandwidth relative to the AC-HBT. The AC-HBT is also shown scaled by 34% to compare more directly to the CB-HBT, which had a larger SET signal.

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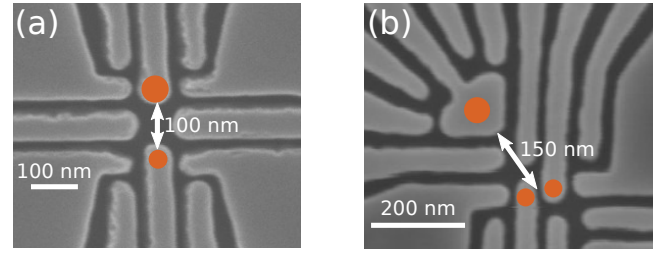


Figure 5. (a) SEM image of Si-MOS device used in CB-HBT circuit. The edge of the SET (larger orange dot) is roughly 100 nm away from the quantum dot (smaller orange dot). (b) SEM image of the Si-MOS device used in the AC-HBT circuit. The proximity of the SET to the double quantum dot system is 50% further away at roughly 150 nm.

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Appendix A: SET Geometries And Details

The SET connected to the AC-HBT uses a single layer doped poly-Si electrode structure on 50 nm thick SiO_2 , providing a mobility of $19,500 \text{ cm}^2/\text{Vs}$ at 4 K. The poly-Si gate layer is etch-defined into electrodes that control the formation of the SET (upper left in Figure 1(a) SEM image) and two quantum dots (under gates RD and LD). Regions of electron enhancement are indicated by the highlighted regions.

The Si-MOS device in the CB-HBT circuit is similar to the Si-MOS device in the AC-HBT circuit with the exception that the SiO_2 layer is 35 nm thick and the bottom layer is isotopically purified silicon (500 ppm ^{29}Si). The ^{28}Si isotope has no net nuclear spin, therefore it is ideal for qubits to be formed in because decoherence due to magnetic noise is highly suppressed. Phosphorous (^{31}P) donor atoms are imbedded in the ^{28}Si layer using ion implantation near where the quantum dot is intended to be formed (red dot in Figure 2(a) SEM image).

The CB-HBT and AC-HBT were characterized using different Si-MOS devices possessing different electrostatic gate layouts (Figure 5). The geometry of the gate layout affects the mutual capacitance between the SET and the quantum dot. More capacitive coupling results in larger

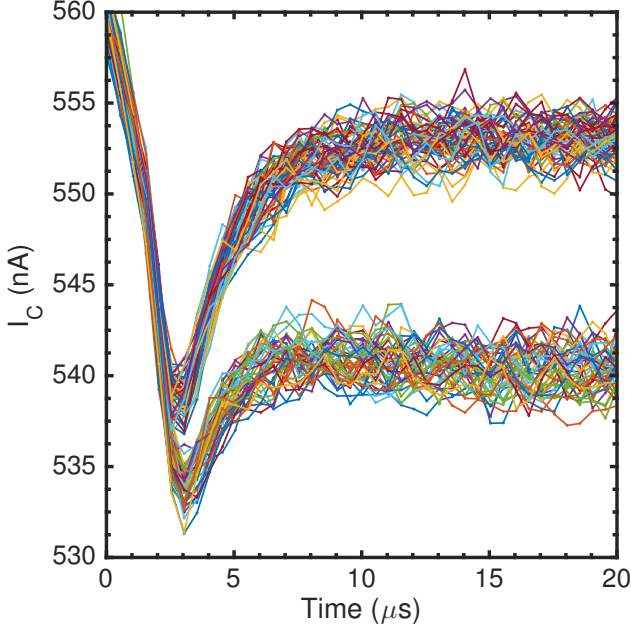


Figure 6. 100 single-shot traces for the CB-HBT charge readout. Slower response time is compensated for by larger signal separation at earlier times relative to the AC-HBT readout.

changes in the electrochemical potential of the charge-sensor for a given quantum dot charging event⁴⁹. Since changes in electrochemical potential of the charge-sensor result in changes in current through the charge-sensor, larger changes result in larger signal. Therefore, more mutual capacitance leads to larger readout signals, faster readout times, and higher readout fidelity.

The gate geometry used in the Si-MOS device connected to the CB-HBT had the SET 33% closer to the quantum dot than in the Si-MOS device connected to the AC-HBT. The closer SET proximity in the CB-HBT resulted in an increase in sensitivity of approximately 34%. We compare the sensitivity of both circuits by dividing the voltage shift of the dot occupancy transition by the charge-sensor Coulomb blockade peak period. For the CB-HBT, the voltage shift was 18 mV and the charge-sensor period was 337 mV (5.34% change). For the AC-HBT, the voltage shift was 12 mV and the charge-sensor period was 350 mV (4% change). Therefore, the SET in the CB-HBT was around 34% more sensitive to charging events than the AC-HBT.

Appendix B: Current-Biasing Effect of CB-HBT Circuit

Since the node that connects the SET source to the HBT base is floating, the bias across the SET cannot be set to a fixed voltage in the CB-HBT circuit. Verilog-A models were created to simulate the behavior of the circuit when biasing the SET through multiple regions of

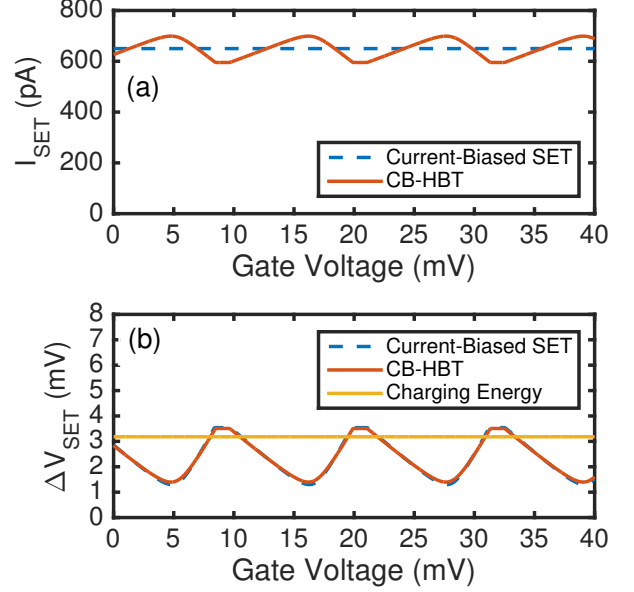


Figure 7. Comparison of CB-HBT and current-biased SET Verilog-A models. The top plot shows the drain current of the SET as a function of gate voltage. The current is modulated much less in this condition than in a constant voltage-biased circuit. The bottom plot shows voltage across the SET as a function of gate voltage. The overlap between the two curves shows that the CB-HBT circuit is effectively equivalent to current-biasing the SET.

Coulomb blockade via an electrostatic gate. As the SET resistance changes due to Coulomb blockade, the source-drain bias across the SET changes to allow current to flow into the base of the HBT (Figure 7(b)). In order for this to happen, the HBT trades base-emitter voltage for minimal impact to operation. Although the trade in voltage results in a relatively small change in HBT collector current during, for example, a single-shot readout event, this signal is approximately 100 larger than the SET source-drain signal without an HBT (e.g. $\Delta I_C = 10$ nA vs. $\Delta I_{SET} = 100$ pA).

The Verilog-A model estimates the small signal resistances as: $r_{set} = 200$ k Ω and $r_{\pi} = 10$ M Ω (where r_{π} is the small signal resistance of the base-emitter junction). Most of the emitter bias voltage is across the base-emitter junction at all times (since $r_{set} \ll r_{\pi}$), therefore the CB-HBT is a current-biasing circuit. The current-biasing behavior is highlighted in Figure 8(a), where three Coulomb blockade peaks are plotted. For comparison, three Coulomb blockade peaks are plotted for the AC-HBT case (Figure 8(b)). The CB-HBT amplified peaks are broadened by the current-biasing effect and the blockade region never reaches zero current as it would with a smaller constant voltage bias. The AC-HBT amplified peaks are much narrower and minimally broaden due to having a constant, small voltage bias regardless of HBT power. Comparable sensitivities can be

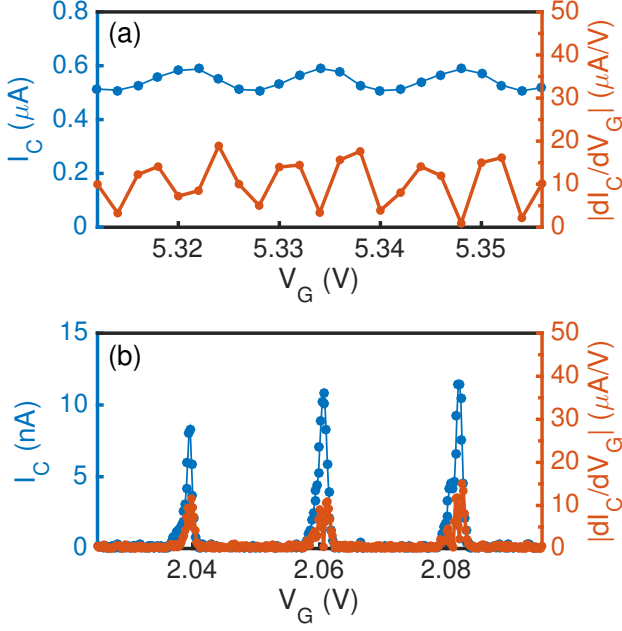


Figure 8. (a) Coulomb blockade peaks for the CB-HBT (blue). The absolute value of the sensitivity is plotted as orange points. Since there is almost always positive or negative blockade slope, the absolute value of the sensitivity remains positive for most of the range plotted. (b) Coulomb blockade peaks for the AC-HBT (blue). The absolute value of the sensitivity is plotted as orange points as well.

achieved for either circuit around $10 \mu A/V$.

Appendix C: Electron Temperature Measurement

Heating of electrons in the quantum dot due to the operation of the connected HBT is a concern, therefore we examined the dependence of electron temperature on HBT amplifier bias (Figure 3(e)). For the CB-HBT, The electron temperature of the QD was measured by extracting the width of a Coulomb blockade peak as a function of fridge temperature. The QD was tuned to a transport regime where the QD was approximately equally tunnel-coupled to both reservoirs and there were around 10 electrons in the QD. The source-drain bias was reduced to $5 \mu V_{rms}$ to avoid bias heating. A Coulomb peak was chosen where a minimum width was observed in Coulomb diamond measurements. After extracting the lever-arm of the gate used to measure the broadening ($13 \mu eV/mV$), we find that the minimum linewidth yields an electron temperature around 150 mK. Heating of the QD begins where the CB-HBT is operating with over 100 gain, therefore the CB-HBT circuit can amplify well while heating the electrons to 160–200 mK.

For the AC-HBT setup, the base electron temperature was around 120 mK. This is confirmed by the measurements of the electron temperature when measuring the SET signal directly through the shunt resistor (R_S in Fig-

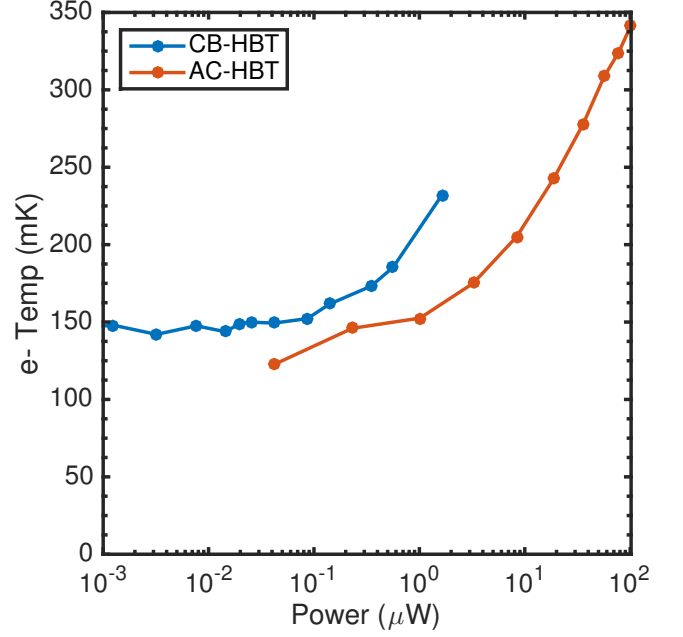


Figure 9. Electron temperature vs. power for both circuits. Base temperatures are between 120–150 mK. Both circuits operate in the 160–200 mK range for single-shot data taken.

ure 1(a)) with the HBT turned off. With the HBT on, The electron temperature is deduced by measuring the Fermi-Dirac linewidth of the (1,0)-(2,0) charge transition. When the AC-HBT bias is increased up to $3.24 \mu W$, the electron temperature remains near the base temperature (Figure 9). For powers above this threshold, the electron temperature increases approximately linearly with power. This might be due to local heating of the PCB and wires, which increase the temperature of the nearby device⁵⁰. No effort has been made to heat sink the AC-HBT in this experiment, so further tests with various heat sinking options will be performed to minimize the increase in electron temperature. Nonetheless, an electron temperature of 200 mK is achieved for the bias condition that provides the minimum amplifier noise.

Appendix D: HBT Characterization

Before being used in either amplification circuit, HBTs are initially characterized in liquid helium at 4 K using PCBs with eight HBTs mounted on them. We find that HBT performance at 4 K—particularly current gain vs. base current—changes minimally when HBTs are cooled down to 20–60 mK in a dilution refrigerator (Figure 10(b)). This is most likely due to the charge-carrier transport mechanism changing from a drift-diffusion regime (temperature dependent) to a tunneling regime (barrier dependent) at around 30 K⁴⁴.

In order to characterize HBTs, Keithley 2400 source-measure units are used as current meters and connected

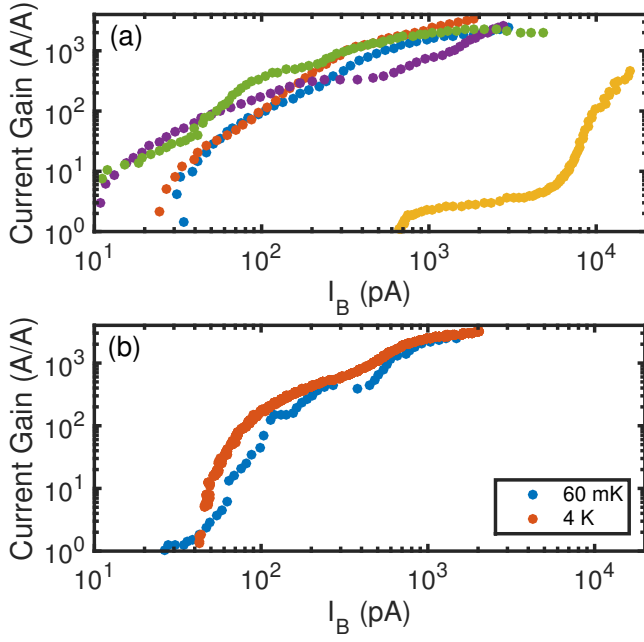


Figure 10. (a) Example plots of current gain vs. base current for different HBTs. Several curves reach current gain > 1000 for base currents < 500 pA. The HBT corresponding to the yellow curve is subpar since it requires base current < 10 nA to reach current gain < 1000 . (b) Current gain vs. base current at different temperatures for HBT used in the CB-HBT circuit. There is a slight difference in the two curves, however the performance at 60 mK is enough to efficiently amplify and perform single-shot readout.

to the HBT base and collector terminals. A power supply (emitter bias) is connected to the HBT emitter terminal and used to bias the HBT to different operating regimes. The emitter bias has to reach approximately -1 V for the HBT to begin operating in an amplifying regime. As the emitter bias is changed from -1.00 V to around -1.07 V, the collector and base current begin to increase exponentially. The current gain, defined by dividing the collector current by the base current, also increases exponentially as emitter bias changes.

Previous measurements without HBT amplification circuits indicate that the SET current should be below several hundred pA in order to avoid QD electron heating. For the CB-HBT, we select HBTs based on their current gain at low base currents. Around 20% of HBTs characterized will have current gain > 100 at base current < 200 pA (Figure 10(a)). For the AC-HBT, the transconductance (g_m) is the only metric required for selection. Since the HBTs were fabricated with g_m as a primary metric, $> 80\%$ of HBTs are usable for the AC-HBT circuit even at low temperatures. However, g_m does not scale ideally in these HBTs at cryogenic temperatures. For a given HBT, $g_m \propto I_C^n$, where $n = 1$ in normal conditions. In the HBTs used in this work, $n \approx 0.8$, which leads to suboptimal SNR at higher power.

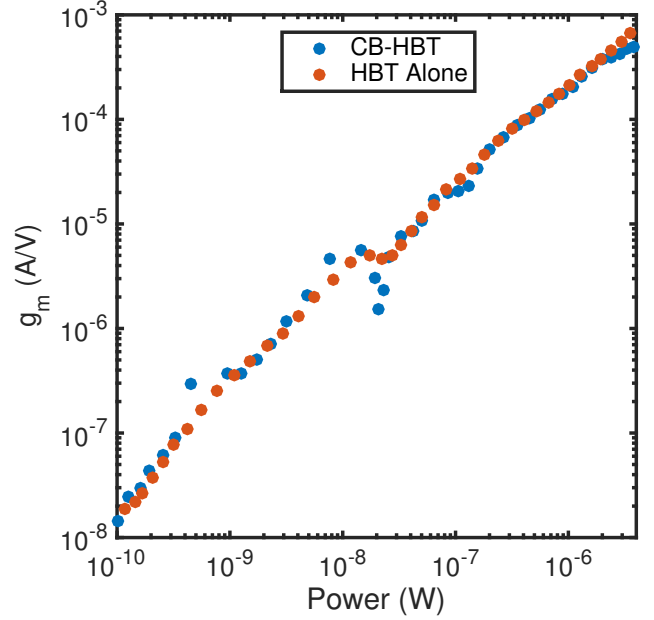


Figure 11. Transconductance vs. power for the CB-HBT (SET connected to HBT) and the same HBT without an SET connected. The data overlaps for both cases, therefore the transconductance can be reliably measured directly in the CB-HBT (assuming $r_{set} \ll r_\pi$).

Appendix E: CB-HBT Small Signal Gain

The gain of the CB-HBT is calculated using a standard BJT small-signal model. A small voltage fluctuation at the base node is usually converted to a large current fluctuation at the collector node by the transconductance, $g_m = \frac{di_c}{dv_{be}}$. This voltage fluctuation is usually the small-signal base-emitter junction resistance, r_π , multiplied by the base current. However, in the case of the CB-HBT, $r_{set} \parallel r_\pi$, therefore the parallel combination of the two resistances is required to calculate gain:

$$\text{gain}_{CB} = \frac{i_c}{i_{set}} = g_m(r_{set} \parallel r_\pi) \quad (\text{E1})$$

Appendix F: Noise Models

Sources of noise in the HBT amplification circuits include: shot noise, Johnson noise, triboelectric noise associated with the coaxial lines coupled to fridge vibration²⁴, room temperature amplifier noise, and other instrumental noise. At relatively low power operation regimes ($< 1 \mu\text{W}$ for the AC-HBT and $< 200 \text{ nW}$ for the CB-HBT), the noise due to vibrations in the fridge dominates at around $1 \text{ pA}/\sqrt{\text{Hz}}$. The input noise spectral density of the room temperature amplifier is relatively low ($100\text{--}500 \text{ fA}/\sqrt{\text{Hz}}$), therefore we focus on noise sources much more dominant. When either circuit is operating in a regime appropriate for single-shot readout, the base shot

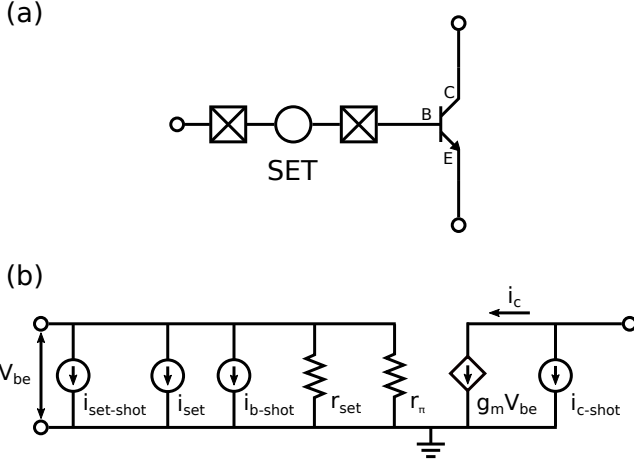


Figure 12. (a) CB-HBT circuit schematic for reference. (b) CB-HBT effective circuit model. The shot noise current source, i_{b-shot} , is in parallel with r_{set} and r_{π} . Most of the shot noise does not enter the base of the HBT because $r_{set} \ll r_{\pi}$. The signal, i_{set} , is also shown, which is amplified according to Equation E1.

noise is greater than the collector shot noise (Figures 1(e) and 2(e)). For the SET shot noise in either case, we do not consider a Fano factor, which would reduce the noise for a given power^{51,52}. The total noise for either circuit is calculated by assuming noise sources are independent processes and adding noise sources in quadrature.

Noise modeling for the CB-HBT circuit is nontrivial because of current division at the HBT base node since $r_{set} \ll r_{\pi}$. The SET and base current are reduced to a Norton equivalent circuit, and the HBT is reduced to r_{π} connected to a current source which takes voltage fluctuations (v_{be}) across r_{π} and converts them to collector current via the transconductance, g_m . For the CB-HBT, the noise model is a shot noise current source ($i_{b-shot} = \sqrt{2eI_B\Delta f}$, where I_B is the DC base current, and Δf is the bandwidth centered on frequency f) in parallel with r_{set} and r_{π} (Figure 12(b)). Since $r_{set} \ll r_{\pi}$, most of the shot noise current goes through the SET to ground, and a much smaller amount enters the HBT base and is amplified. The amplified base shot noise is shown in Equation F1:

$$i_{b-shot-amp} = i_{b-shot} \text{gain}_{CB} = i_{b-shot} g_m (r_{set} || r_{\pi}) \quad (\text{F1})$$

This amplified base shot noise is estimated in Figure 2(e) as the orange curve where g_m and r_{π} are calculated from Gummel plots of the HBT and r_{set} is assumed to be 3

M Ω , which was verified in later measurements with the HBT disconnected from the Si-MOS device.

The noise model for the AC-HBT is similar to the CB-HBT with r_s and r_B added in parallel to r_{set} and r_{π} . The coupling capacitor, C , is considered a short at the frequencies appropriate to model noise in the AC-HBT. The Johnson noise of R_S in the AC-HBT circuit is $v_{s-jn} = \sqrt{4k_B T R_S \Delta f}$ (where T is the temperature)

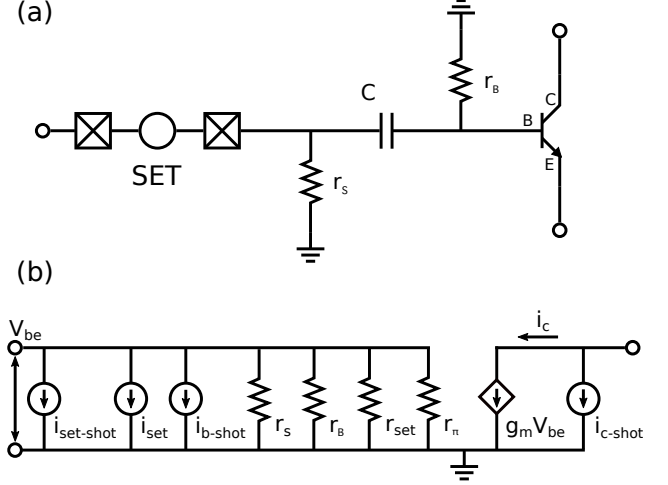


Figure 13. (a) AC-HBT circuit schematic for reference. (b) AC-HBT effective circuit model with signal, i_{set} , also shown. The model is similar to the CB-HBT with two new resistors added in parallel, r_s and r_B .

and does not contribute significantly in the single-shot operation regime. Since the AC-HBT has a separate current to bias the base-emitter junction, $I_{SET} \neq I_B$, therefore the base shot noise and SET shot noise are considered separately. However, $I_{SET} < I_B$, so the base shot noise is always dominant in amplifying regimes.

Appendix G: AC-HBT Bias Tee Parameters

The bias tee parameters for the AC-HBT were chosen to be $R_S = 100 \text{ k}\Omega$ and $C = 10 \text{ nF}$, which sets a high pass filter at 160 Hz. Operating the circuit at frequencies higher than 160 Hz aids in avoiding higher noise levels at lower frequency due to 1/f-like noise behavior in the system.

The shunt resistance value is chosen to be less than r_{set} (100s of k Ω) so that most of the SET bias voltage drops across the SET.